



ELECTRONICS, INC.
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NTE127 Germanium PNP Transistor Horizontal Output Amplifier

Absolute Maximum Ratings:

Collector–Base Voltage, V_{CBO}	Peak	320V
	Continuous	60V
Emitter–Base Voltage, V_{EBO}	2V
Collector Current, I_C	10A
Base Current, I_B	+4, -1A
Power Dissipation ($T_{MF} \leq +55^\circ\text{C}$), P_D	5W
Operating Junction Temperature Range, $T_{J(opr)}$	-65° to +85°C
Storage Temperature Range, T_{stg}	-65° to +85°C
Maximum Thermal Resistance, Junction–to–Case, R_{thJC}	1.5°C/W
Lead Temperature (During Soldering, 10sec Max), T_L	+230°C

Electrical Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C = 0.025\text{A}, V_{EB} = 0$	320	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\text{mA}, I_C = 0$	2	–	–	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 10\text{V}, I_E = 0$	–	–	200	μA
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 6\text{A}, I_B = 400\text{mA}$	–	–	1.5	V
		$I_C = 3\text{A}, I_B = 200\text{mA}$	–	–	1.5	V
DC Current Gain	h_{FE}	$V_{CE} = 3\text{V}, I_C = 6\text{A}$	15	–	–	
Base–Emitter Voltage	V_{BE}	$I_C = 6\text{A}, I_B = 400\text{mA}$	–	0.8	–	V
Turn–Off Time	$t_s + t_f$		–	–	1.2	μs

Note 1. This device is for **replacement only** and **NOT** intended for new design. Therefore, these specifications are for **reference only** and strictly for determining the suitability of this device as a replacement in a working circuit.



